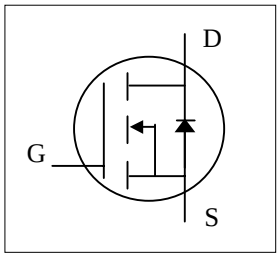
XP65SL190DWL

Halogen-Free Product

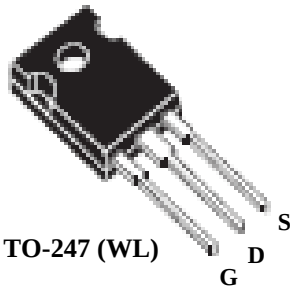
N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

- **100% R_g & UIS Test**
- **Low t_{rr} / Q_{rr}**
- **Simple Drive Requirement**
- **RoHS Compliant & Halogen-Free**



BV_{DSS}	650V
$R_{DS(ON)}$	0.19Ω
I_D[3]	20A



TO-247 (WL)

Description

XP65SL190D series are innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.
The TO-247 package is widely preferred for commercial-industrial applications. The device is suited for switch mode power supplies, DC-AC converters and high current high speed switching circuits.

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	±20	V
V_{GS}	Gate-Source Voltage, AC (f > 1Hz)	±30	V
I_D@T_C=25℃	Drain Current, V_{GS} @ 10V[3]	20	A
I_D@T_C=100℃	Drain Current, V_{GS} @ 10V[3]	12.3	A
I_{DM}	Pulsed Drain Current[1]	48	A
dv/dt	MOSFET dv/dt Ruggedness (V_{DS} = 0 …400V)	20	V/ns
P_D@T_C=25℃	Total Power Dissipation	147	W
P_D@T_A=25℃	Total Power Dissipation	3.12	W
E_{AS}	Single Pulse Avalanche Energy[4]	300	mJ
dv/dt	Peak Diode Recovery dv/dt[5]	15	V/ns
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	0.85	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient	40	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	650	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=6.2A	-	-	0.19	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	2	-	5	V
g_{fs}	Forward Transconductance	V_{DS}=15V, I_D=7.5A	-	12	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=520V, V_{GS}=0V	-	-	100	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V, V_{DS}=0V	-	-	±1	uA
Q_g	Total Gate Charge	I_D=7.5A	-	58	92.8	nC
Q_{gs}	Gate-Source Charge	V_{DS}=520V	-	13	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=10V	-	26	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=300V	-	17	-	ns
t_r	Rise Time	I_D=7.5A	-	19	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω	-	57	-	ns
t_f	Fall Time	V_{GS}=10V	-	16	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	2070	3312	pF
C_{oss}	Output Capacitance	V_{DS}=100V	-	60	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	5	-	pF
R_g	Gate Resistance	f=1.0MHz	-	4.1	8.2	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=6.2A, V_{GS}=0V	-	0.8	-	V
t_{rr}	Reverse Recovery Time	I_S=11A, V_{GS}=0V	-	155	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	1.2	-	μC

Notes:

1.Pulse width limited by max. junction temperature.

2.Pulse test

3.Limited by max. junction temperature. Maximum duty cycle D=0.75

4.Starting T_j=25°C , V_{DD}=50V , L=150mH , R_G=25Ω , V_{GS}=10V

5.I_{SD} ≦ I_D, V_{DD} ≦ BV_{DSS}, starting T_J = 25°C

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.
USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.
YAGEO XSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.
YAGEO XSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.

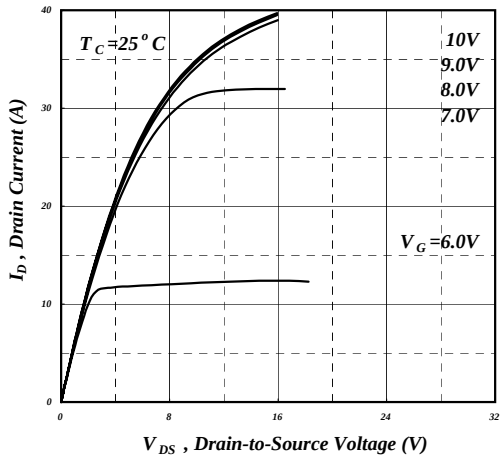


Fig 1. Typical Output Characteristics

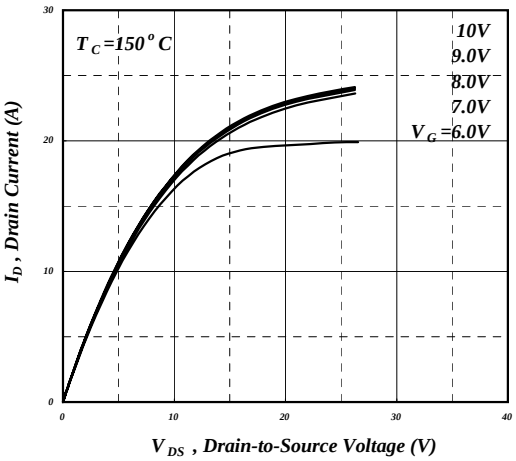


Fig 2. Typical Output Characteristics

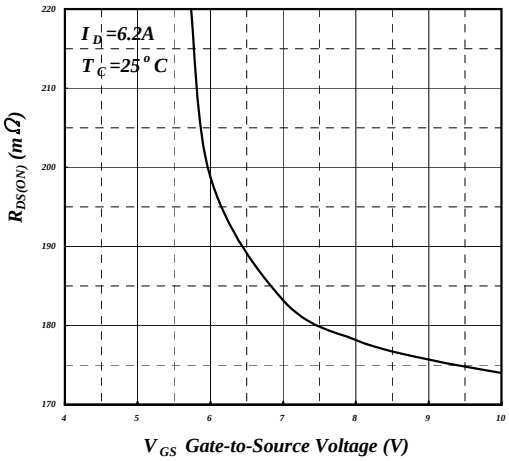


Fig 3. On-Resistance v.s. Gate Voltage

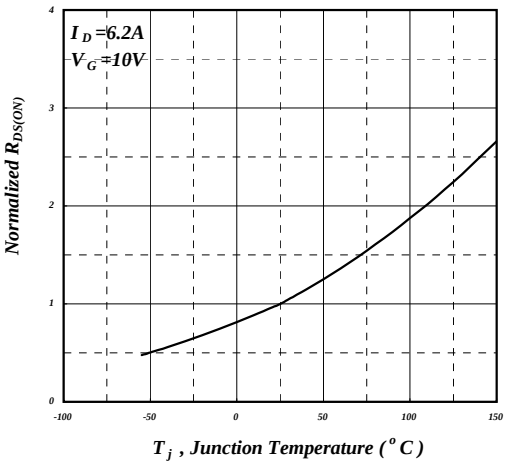


Fig 4. Normalized On-Resistance v.s. Junction Temperature

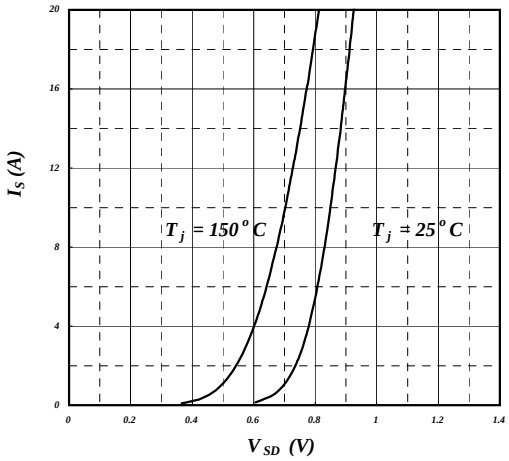


Fig 5. Forward Characteristic of Reverse Diode

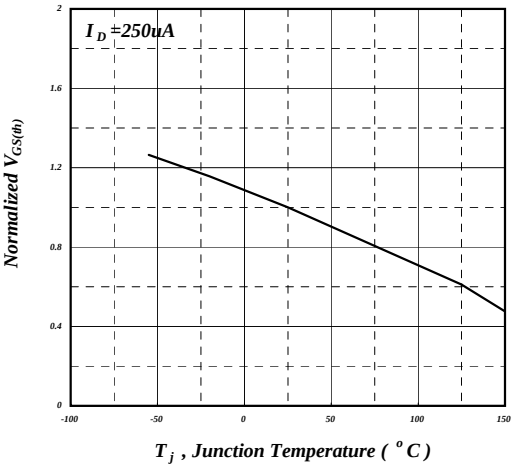


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

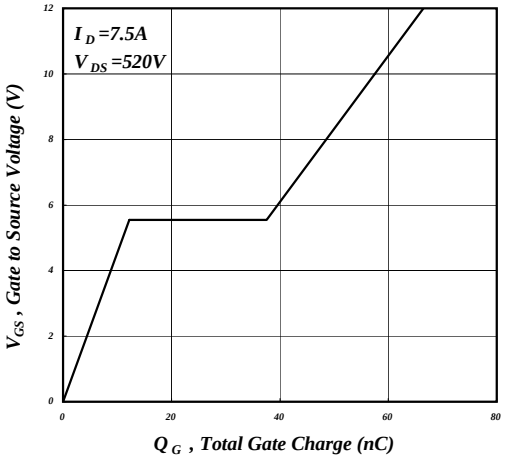


Fig 7. Gate Charge Characteristics

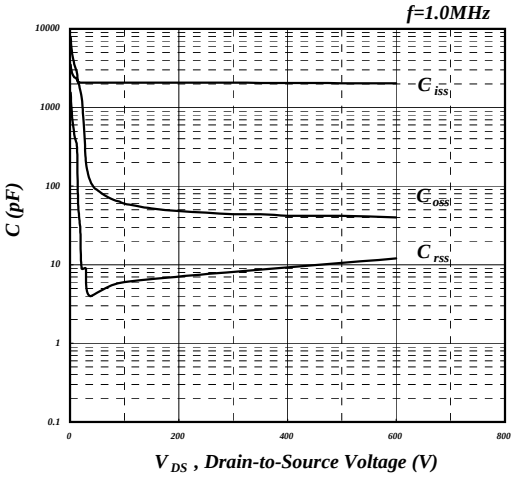


Fig 8. Typical Capacitance Characteristics

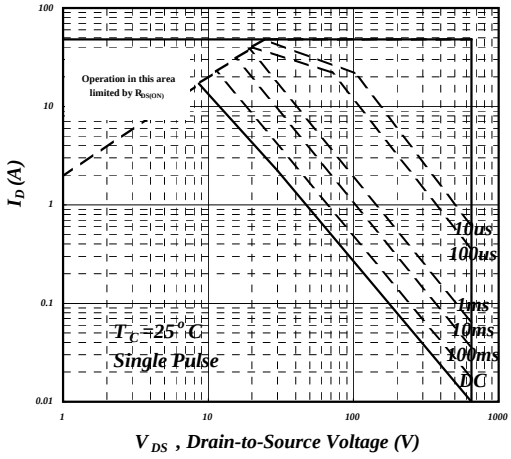


Fig 9. Maximum Safe Operating Area

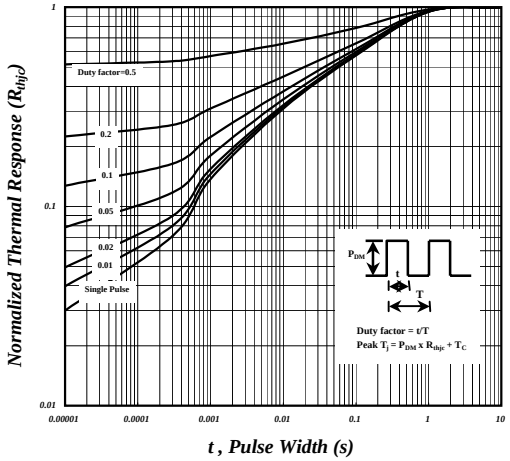


Fig10. Effective Transient Thermal Impedance

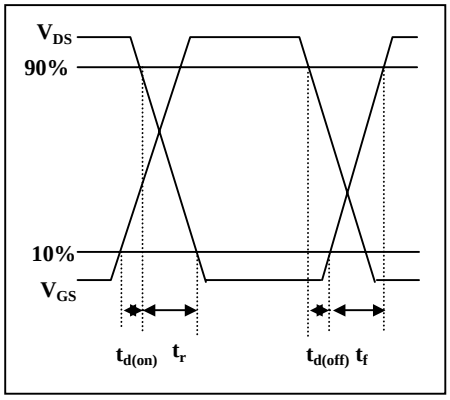


Fig 11. Switching Time Waveform

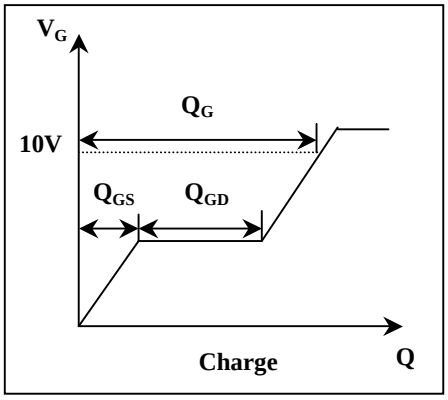


Fig 12. Gate Charge Waveform

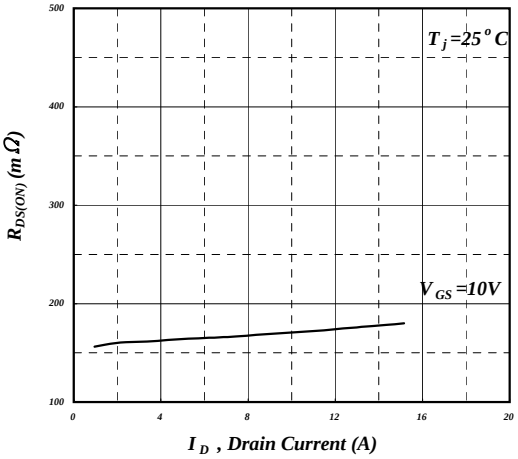


Fig 13. Typ. Drain-Source on State Resistance

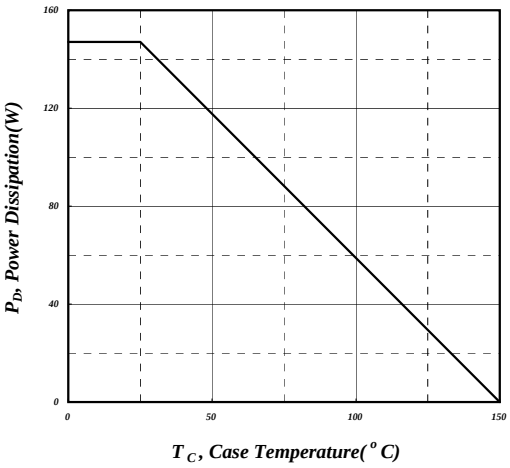
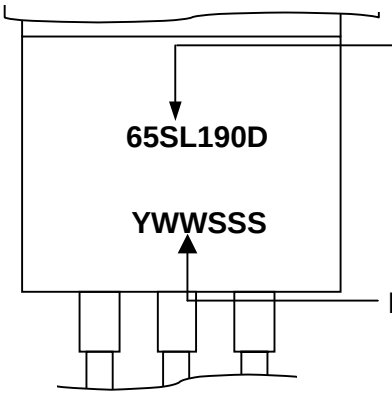
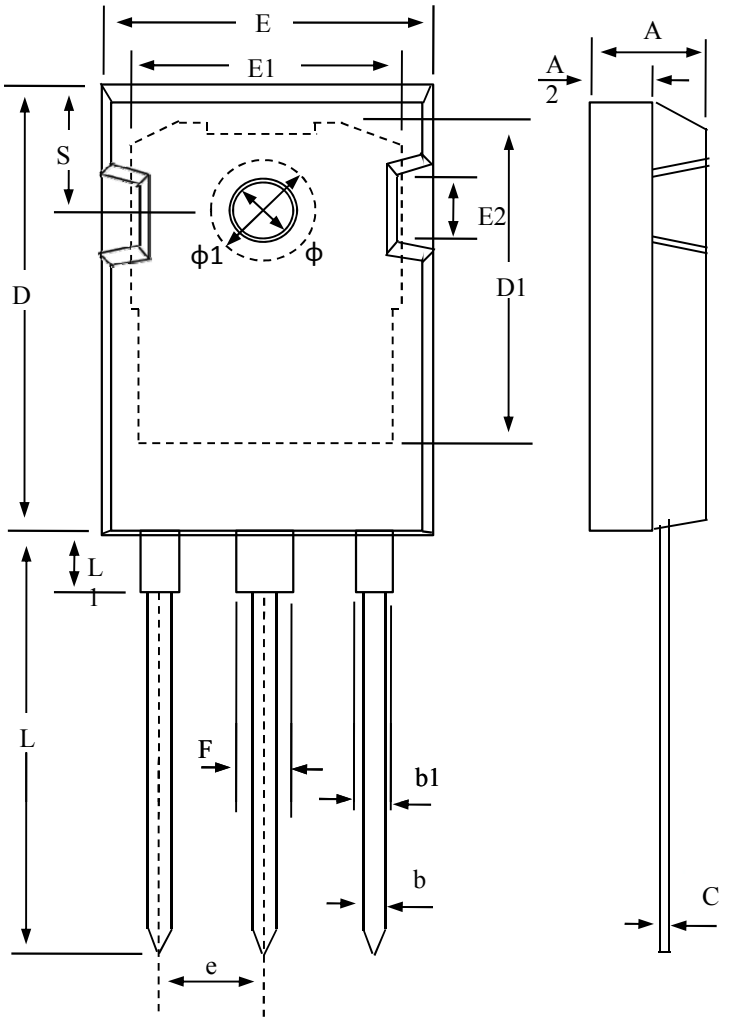


Fig 14. Total Power Dissipation

MARKING INFORMATION



Package Outline : TO-247



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.80	5.03	5.25
A2	1.90	2.05	2.20
E	15.75	15.95	16.15
E1	13.00	13.60	14.20
E2	3.60	4.35	5.10
D	20.80	20.95	21.10
D1	16.20	16.95	17.70
C	0.50	0.60	0.70
L	19.80	20.10	20.40
L1	4.10	4.25	4.40
F	2.80	3.10	3.40
b	1.05	1.20	1.35
b1	1.90	2.18	2.45
e	5.44 ref.		
φ	3.50	3.58	3.65
φ1	7.18 ref.		
S	6.00	6.15	6.30

1.All Dimensions Are in Millimeters.

2.Dimension Does Not Include Mold Protrusions.

Draw No. M1-WL3-G-v02

TO-247 FOOTPRINT：